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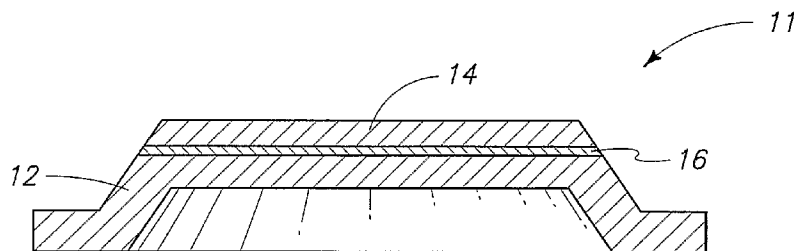
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(54) Title: HIGH PURITY NICKEL/VANADIUM SPUTTERING COMPONENTS; AND METHODS OF MAKING SPUTTERING COMPONENTS



(57) Abstract: The invention includes sputtering components, such as sputtering targets, comprising high-purity Ni-V. The sputtering components can have a fine average grain size throughout, with an exemplary fine average grain size being a grain size less than or equal to 40 microns. The invention also includes methods of making high-purity Ni-V structures.

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